

N-Channel Reduced Q_g , Fast Switching MOSFET

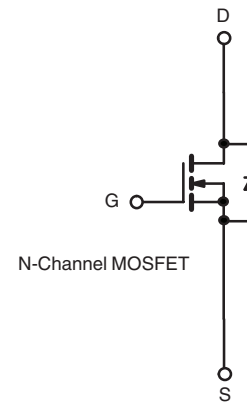
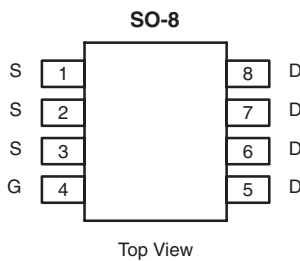
| PRODUCT SUMMARY | | |
|-----------------|---------------------------|-----------|
| V_{DS} (V) | $R_{DS(on)}$ (Ω) | I_D (A) |
| 30 | 0.0085 at $V_{GS} = 10$ V | ± 13 |
| | 0.014 at $V_{GS} = 4.5$ V | ± 10 |

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFETS
- High-Efficiency
- PWM Optimized
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE
Available



Ordering Information: Si4880DY-T1-E3 (Lead (Pb)-free)
Si4880DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

| ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted | | | |
|--|----------------|---------------|----------|
| Parameter | Symbol | Limit | Unit |
| Drain-Source Voltage | V_{DS} | 30 | V |
| Gate-Source Voltage | V_{GS} | ± 25 | |
| Continuous Drain Current ($T_J = 150$ °C) ^{a, b} | I_D | $T_A = 25$ °C | ± 13 |
| | | $T_A = 70$ °C | ± 10 |
| Pulsed Drain Current (10 μ s Pulse Width) | I_{DM} | ± 50 | A |
| Continuous Source Current (Diode Conduction) ^{a, b} | I_S | 2.3 | |
| Maximum Power Dissipation ^{a, b} | P_D | $T_A = 25$ °C | 2.5 |
| | | $T_A = 70$ °C | 1.6 |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | - 55 to 150 | °C |

| THERMAL RESISTANCE RATINGS | | | | | |
|---|---------------|------------|---------|---------|------|
| Parameter | | Symbol | Typical | Maximum | Unit |
| Maximum Junction-to-Ambient (MOSFET) ^a | $t \leq 10$ s | R_{thJA} | | 50 | °C/W |
| | Steady State | | 70 | | |

Notes:

a. Surface mounted on FR4 board.

b. $t \leq 10$ s.

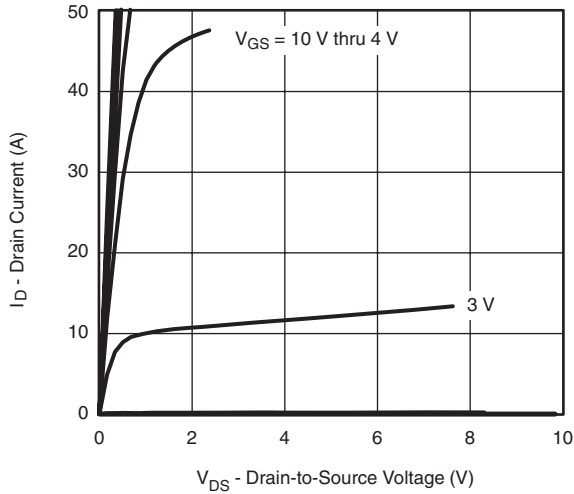
| MOSFET SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted | | | | | | |
|---|--------------|--|------|--------|-----------|---------------|
| Parameter | Symbol | Test Conditions | Min. | Typ. | Max. | Unit |
| Static | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$ | 0.8 | | 1.8 | V |
| Gate-Body Leakage | I_{GSS} | $V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$ | | | ± 100 | nA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$ | | | 1 | μA |
| | | $V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$ | | | 5 | |
| On-State Drain Current ^a | $I_{D(on)}$ | $V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$ | 40 | | | A |
| Drain-Source On-State Resistance ^a | $R_{DS(on)}$ | $V_{GS} = 10\text{ V}, I_D = 13\text{ A}$ | | 0.0069 | 0.0085 | Ω |
| | | $V_{GS} = 4.5\text{ V}, I_D = 10\text{ A}$ | | 0.0115 | 0.014 | |
| Forward Transconductance ^a | g_{fs} | $V_{DS} = 15\text{ V}, I_D = 13\text{ A}$ | | 26 | | S |
| Diode Forward Voltage ^a | V_{SD} | $I_S = 2.3, V_{GS} = 0\text{ V}$ | | 0.70 | 1.1 | V |
| Dynamic^b | | | | | | |
| Total Gate Charge | Q_g | $V_{DS} = 15\text{ V}, V_{GS} = 5.0\text{ V}, I_D = 13\text{ A}$ | | 19.5 | 25 | nC |
| Gate-Source Charge | Q_{gs} | | | 4.2 | | |
| Gate-Drain Charge | Q_{gd} | | | 8.8 | | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD} = 15\text{ V}, R_L = 15\text{ }\Omega$ $I_D \cong 1\text{ A}, V_{GEN} = 10\text{ V}, R_g = 6\text{ }\Omega$ | | 14 | 22 | ns |
| Rise Time | t_r | | | 9 | 15 | |
| Turn-Off Delay Time | $t_{d(off)}$ | | | 46 | 70 | |
| Fall Time | t_f | | | 30 | 45 | |
| Source-Drain Reverse Recovery Time | t_{rr} | $I_F = 2.3\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$ | | 35 | 70 | |

Notes:

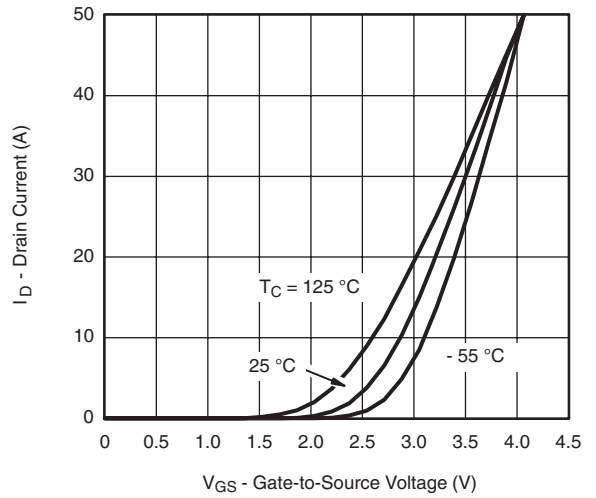
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

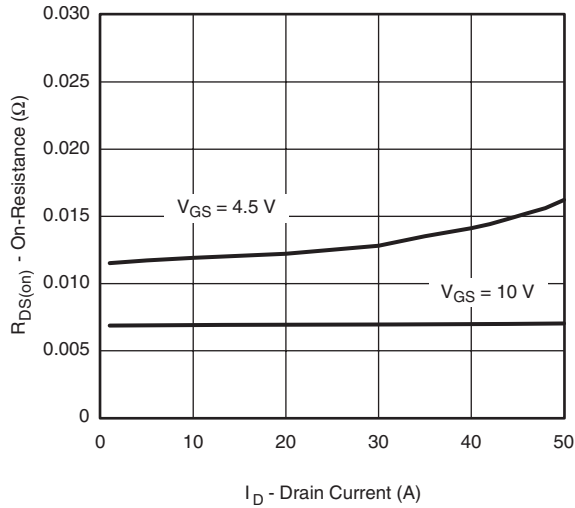
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



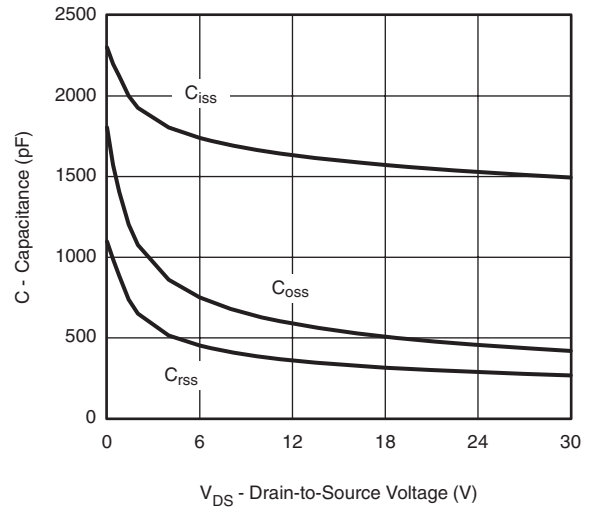
Output Characteristics



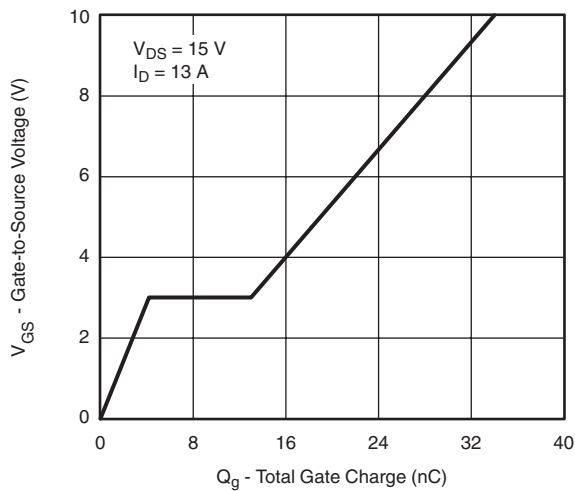
Transfer Characteristics



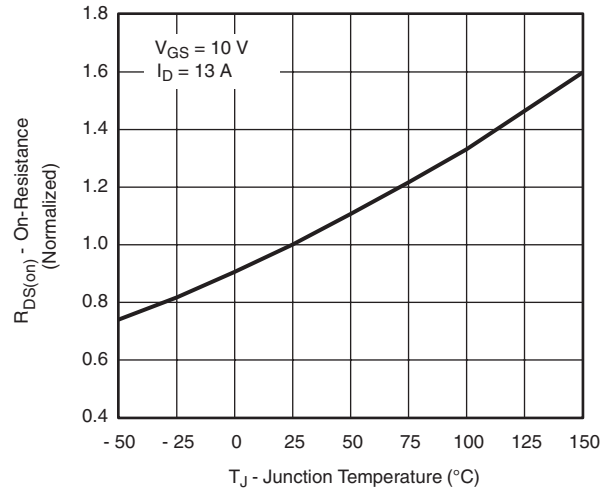
On-Resistance vs. Drain Current



Capacitance

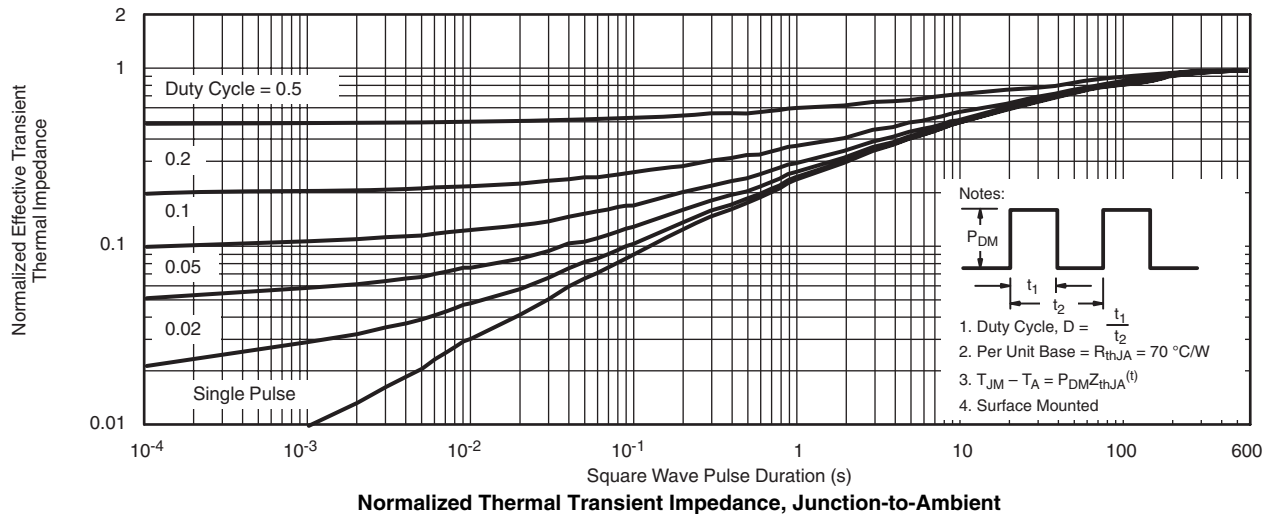
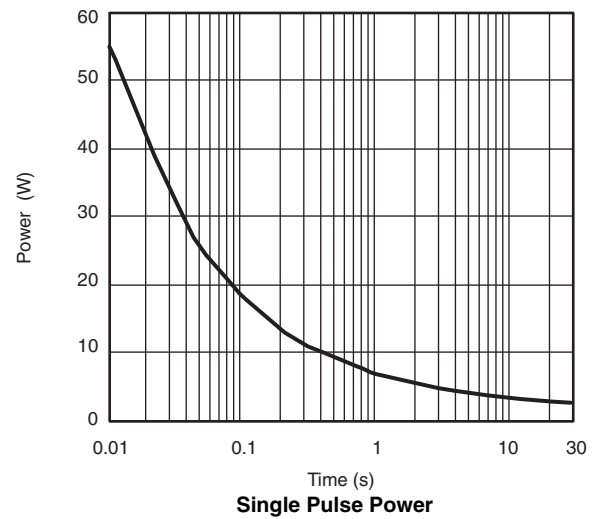
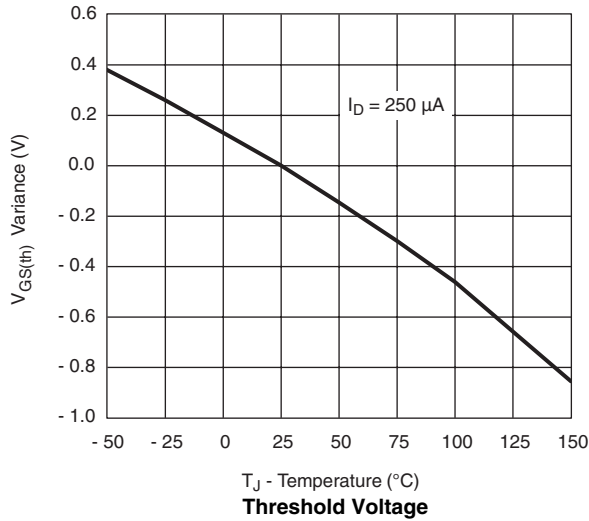
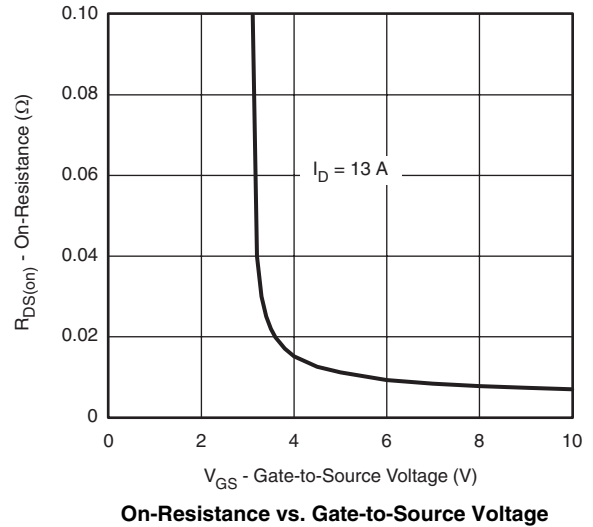
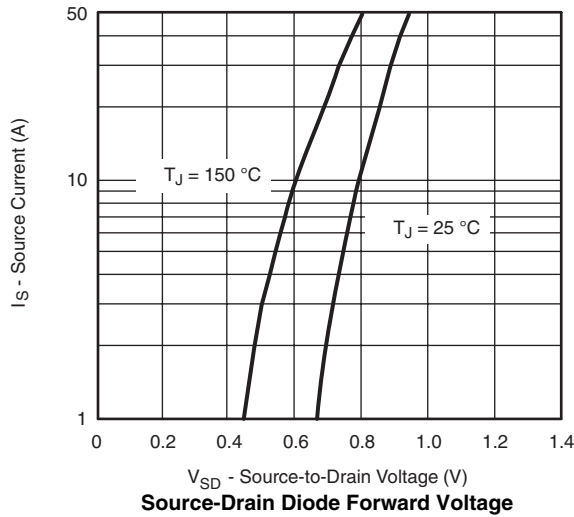


Gate Charge



On-Resistance vs. Junction Temperature

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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